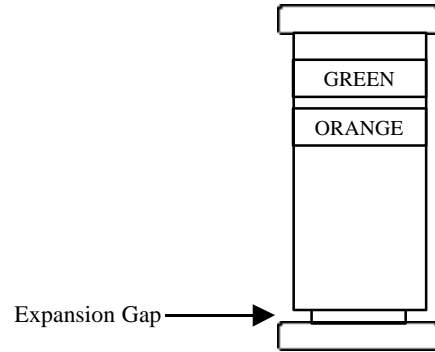


BAV103

General Description:

A General Purpose diode that couples high forward conductance fast switching speed and high blocking voltages in a glass leadless LL-34 Surface Mount package.

Placement of the Expansion Gap has no relationship to the location of the Cathode Terminal which is indicated by the first color band.



High Voltage, General Purpose Diode

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Sym	Parameter	Value	Units
T _{stg}	Storage Temperature	-65 to +200	°C
T _J	Operating Junction Temperature	-65 to +200	°C
P _D	Total Power Dissipation at T _A = 25°C	500	mW
	Linear Derating Factor from T _A = 25°C	3.33	mW/°C
R _{OJA}	Thermal Resistance Junction-to-Ambient	350	°C/W
W _{IV}	Working Inverse Voltage	200	V
I _O	Average Rectified Current	200	mA
I _F	DC Forward Current (I _F)	500	mA
i _f	Recurrent Peak Forward Current	600	mA
i _{F(surge)}	Peak Forward Surge Current (I _{FSM}) Pulse Width = 1.0 second	1.0	Amp
		4.0	Amp

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired

Electrical Characteristics TA = 25°C unless otherwise noted

SYM	CHARACTERISTICS	MIN	MAX	UNITS	TEST CONDITIONS
B _V	Breakdown Voltage	250		V	I _R = 100 uA
I _R	Reverse Leakage		100	nA	V _R = 200 V V _R = 200 V T _A = 150°C
			100	uA	
V _F	Forward Voltage		1.00	V	I _F = 100 mA I _F = 200 mA
			1.25	V	
C _T	Capacitance		5.0	pF	V _R = 0.0 V, f = 1.0 MHz
T _{RR}	Reverse Recovery Time		50	ns	I _F = I _R 30 mA I _{RR} = 1.0 mA R _L = 100 Ohms

THE PLACEMENT OF THE EXPANSION GAP HAS NO RELATIONSHIP TO THE LOCATION OF THE CATHODE TERMINAL OF THE DEVICE. THE EXPANSION GAP & CATHODE BAND CAN BE ON THE SAME TERMINAL OR AT OPPOSITE TERMINALS OF THE DIODE.

